

# 2SB946

## Silicon PNP epitaxial planar type

For power switching

Complementary to 2SD1271

### Features

- Low collector to emitter saturation voltage  $V_{CE(sat)}$
- Satisfactory linearity of forward current transfer ratio  $h_{FE}$
- Large collector current  $I_C$
- 0Full-pack package which can be installed to the heat sink with one screw

### Absolute Maximum Ratings ( $T_C=25^\circ\text{C}$ )

| Parameter                    | Symbol    | Rated       | Unit             |
|------------------------------|-----------|-------------|------------------|
| Collector to base voltage    | $V_{CBO}$ | -130        | V                |
| Collector to emitter voltage | $V_{CEO}$ | -80         | V                |
| Emitter to base voltage      | $V_{EBO}$ | -7          | V                |
| Peak collector current       | $I_{CP}$  | -15         | A                |
| Collector current            | $I_C$     | -7          | A                |
| Collector power dissipation  | $P_C$     | 40          | W                |
|                              |           | 2           |                  |
| Junction temperature         | $T_j$     | 150         | $^\circ\text{C}$ |
| Storage temperature          | $T_{stg}$ | -55 to +150 | $^\circ\text{C}$ |

### Electrical Characteristics ( $T_C=25^\circ\text{C}$ )

| Parameter                               | Symbol        | Conditions  | min | typ | max  | Unit          |
|---|---------------|---|-----|-----|------|---------------|
| Collector cutoff current                | $I_{CBO}$     | $V_{CB} = -100\text{V}$ , $I_E = 0$                                   |     |     | -10  | $\mu\text{A}$ |
| Emitter cutoff current                  | $I_{EBO}$     | $V_{EB} = -5\text{V}$ , $I_C = 0$                                     |     |     | -50  | $\mu\text{A}$ |
| Collector to emitter voltage            | $V_{CEO}$     | $I_C = -10\text{mA}$ , $I_B = 0$                                      | -80 |     |      | V             |
| Forward current transfer ratio          | $h_{FE1}$     | $V_{CE} = -2\text{V}$ , $I_C = -0.1\text{A}$                          | 45  |     |      |               |
|   | $h_{FE2}^*$   | $V_{CE} = -2\text{V}$ , $I_C = -3\text{A}$                            | 90  |     | 260  |               |
| Collector to emitter saturation voltage | $V_{CE(sat)}$ | $I_C = -5\text{A}$ , $I_B = -0.25\text{A}$                            |     |     | -0.5 | V             |
| Base to emitter saturation voltage      | $V_{BE(sat)}$ | $I_C = -5\text{A}$ , $I_B = -0.25\text{A}$                            |     |     | -1.5 | V             |
| Transition frequency                    | $f_T$         | $V_{CE} = -10\text{V}$ , $I_C = -0.5\text{A}$ , $f = 10\text{MHz}$    |     | 30  |      | MHz           |
| Turn-on time                            | $t_{on}$      | $I_C = -3\text{A}$ , $I_{B1} = -0.3\text{A}$ , $I_{B2} = 0.3\text{A}$ |     | 0.5 |      | $\mu\text{s}$ |
| Storage time                            | $t_{stg}$     |   |     | 1.5 |      | $\mu\text{s}$ |
| Fall time                               | $t_f$         |   |     | 0.1 |      | $\mu\text{s}$ |

\* $h_{FE2}$  Rank classification

| Rank      | Q         | P          |
|-----------|-----------|------------|
| $h_{FE2}$ | 90 to 180 | 130 to 260 |

Note: Ordering can be made by the common rank (PQ rank  $h_{FE2} = 90$  to 260) in the rank classification.





